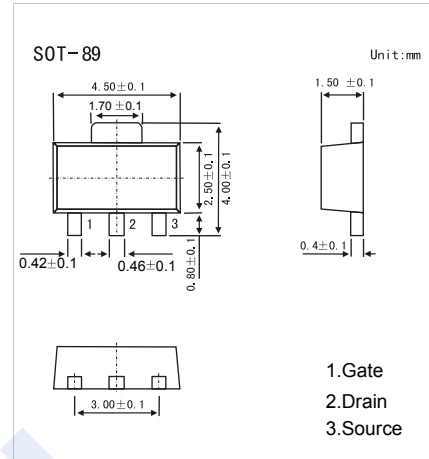
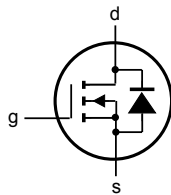


N-Channel MOSFET

BSS87 (KSS87)

■ Features

- $V_{DS} (V) = 200V$
- $I_D = 0.28 A$ ($V_{GS} = 10V$)
- $R_{DS(ON)} < 6 \Omega$ ($V_{GS} = 10V$)
- High-speed switching
- No secondary breakdown.

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	200	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current	I_D	0.28	A
Pulsed Drain Current	I_{DM}	1.1	
Power Dissipation	P_D	1	W
Thermal Resistance Junction- to-Ambient	R_{thJA}	125	$^\circ C/W$
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature Range	T_{stg}	-65 to 150	

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DS}	$I_D = 250 \mu A, V_{GS} = 0V$	200			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 60V, V_{GS} = 0V$			0.2	μA
		$V_{DS} = 200V, V_{GS} = 0V$			60	
Gate-Body Leakage Current	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 1mA$	0.8		2.8	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 0.4A$			6	Ω
Forward Transconductance	g_{FS}	$V_{DS} = 25V, I_D = 0.4A$		350		mS
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = 25V$			60	pF
Output Capacitance	C_{oss}				25	
Reverse Transfer Capacitance	C_{rss}				10	
Turn-On DelayTime	$t_{d(on)}$	$V_{GS} = 0 \text{ to } 10V, V_{DS} = 50V, I_D = 250mA$			10	ns
Turn-Off DelayTime	$t_{d(off)}$				25	

■ Marking

Marking	KA
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N-Channel MOSFET

BSS87 (KSS87)

■ Typical Characteristics

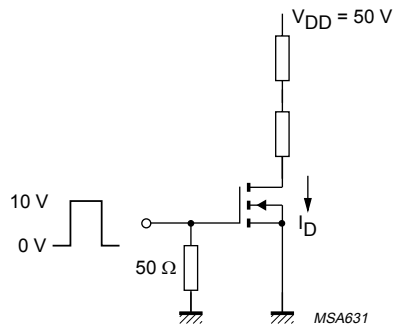


Fig.1 Switching times test circuit.

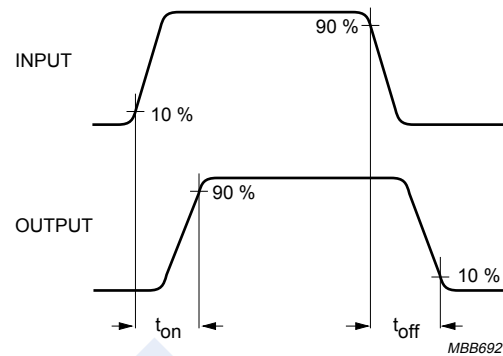


Fig.2 Input and output waveforms.